Rochester Electronics

Datasheet

PART NUMBER

SN55450BJ-ROCV

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer. (OCM)

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
    - Class Q Military
    - Class V Space Level

Qualified Suppliers List of Distributors (QSLD)

- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

SN55450B THRU SN55454B
SN75451B THRU SN75454B
DUAL PERIPHERAL DRIVERS

D2217, DECEMBER 1976—REVISED SEPTEMBER 1986

T-52-17

PERIPHERAL DRIVERS FOR HIGH-CURRENT SWITCHING AT VERY HIGH SPEEDS

- Characterized for Use to 300 mA
- High-Voltage Outputs
- No Output Latch-Up at 20 V (After Conducting 300 mA)
- High-Speed Switching
- Circuit Flexibility for Varied Applications
- TTL-Compatible Diode-Clamped Inputs
- Standard Supply Voltages
- New Plastic DIP (P) with Copper Lead Frame Provides Cooler Operation and Improved Reliability
- Package Options Include Plastic "Small Outline" Packages, Ceramic Chip Carriers, and Standard Plastic and Ceramic 300-mil DIPs

SUMMARY OF SERIES 55450B/75451B

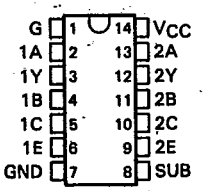
DEVICE	LOGIC OF COMPLETE CIRCUIT	PACKAGES
SN55450B	AND†	FK,J
SN55451B	AND	FK,JG
SN55452B	NAND	FK,JG
SN55453B	OR	FK,JG
SN55454B	NOR	FK,JG
SN75451B	AND	D,P
SN75452B	NAND	D,P
SN75453B	OR	D,P
SN75454B	NOR	D,P

†With output transistor base connected externally to output of gate.

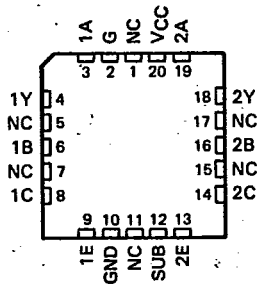
description

Series 55450B/75451B dual peripheral drivers are a family of versatile devices designed for use in systems that employ TTL logic. This family is functionally interchangeable with and replaces the 75450 family and the 75450A family devices manufactured previously. The speed of the 55450B/75451B family is equal to that of the 75450 family, and the parts have been designed to ensure freedom from latch-up. Diode-clamped inputs simplify circuit design.

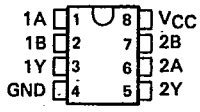
SN55450B . . . J PACKAGE
(TOP VIEW)



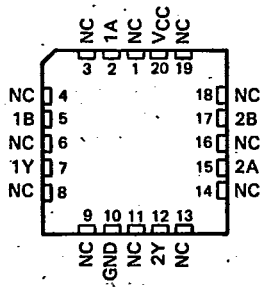
SN55450B . . . FK PACKAGE
(TOP VIEW)



SN55451B, SN55452B,
SN55453B, SN55454B . . . JG PACKAGE
SN75451B, SN75452B,
SN75453B, SN75454B . . . D OR P PACKAGE
(TOP VIEW)



SN55451B, SN55452B,
SN55453B, SN55454B, . . . FK PACKAGE
(TOP VIEW)



NC—No internal connection

5 Peripheral Drivers/Actuators

PRODUCTION DATA documents contain information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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SN55450B THRU SN55454B
SN75451B THRU SN75454B
DUAL PERIPHERAL DRIVERS

description (cont'd)

Typical applications include high-speed logic buffers, power drivers, relay drivers, lamp drivers. MOS drivers, line drivers, and memory drivers.

The SN55450B is a unique general-purpose device, featuring two standard Series 54 TTL gates and two uncommitted, high-current, high-voltage n-p-n transistors. The device offers the system designer the flexibility of tailoring the circuit to the application.

The SN55451B/SN75451B, SN55452B/SN75452B, SN55453B/SN75453B, and SN55454B/SN75454B are dual peripheral AND, NAND, OR, and NOR drivers, respectively, (assuming positive logic), with the output of the logic gates internally connected to the bases of the n-p-n output transistors.

Series 55450B drivers are characterized for operation over the full military range of −55°C to 125°C. Series 75451B drivers are characterized for operation from 0°C to 70°C.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

		SN55450B	SN55451B SN55452B SN55453B SN55454B	SN75451B SN75452B SN75453B SN75454B	UNIT
Supply voltage, V_{CC} (see Note 1)		7	7	7	V
Input voltage		5.5	5.5	5.5	V
Interemitter voltage (see Note 2)		5.5	5.5	5.5	V
V_{CC}-to-substrate voltage		35			V
Collector-to-substrate voltage		35			V
Collector-base voltage		35			V
Collector-emitter voltage (see Note 3)		30			V
Emitter-base voltage		5			V
Off-state output voltage			30	30	V
Continuous collector or output current (see Note 4)		400	400	400	mA
Peak collector or output current ($t_W \leq 10$ ms, duty cycle ≤ 50%, (see Note 4)		500	500	500	mA
Continuous total dissipation at (or below) 25°C free-air temperature (see Note 5)	D package			725	mW
	FK package	1375	1375		
	J package	1375			
	JG package		1050		
	P package			1200	
Operating free-air temperature range		−55 to 125	−55 to 125	0 to 70	°C
Storage temperature range		−65 to 150	−65 to 150	−65 to 150	°C
Case temperature for 60 seconds	FK package	260	260		°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds	J or JG package	300	300		°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	D or P package			260	°C

NOTES: 1. Voltage values are with respect to the network ground terminal unless otherwise specified.
2. This is the voltage between two emitters of a multiple-emitter transistor.
3. This value applies when the base-emitter resistance (R_{BE}) is equal to or less than 500 Ω.
4. Both halves of these dual circuits may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous dissipation rating.
5. For operation above 25°C free-air temperature, refer to the Dissipation Derating Table.

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DISSIPATION DERATING TABLE

PACKAGE	POWER RATING	DERATING FACTOR	ABOVE T_A
D	725 mW	5.8 mW/°C	25°C
FK	1375 mW	11.0 mW/°C	25°C
J	1375 mW	11.0 mW/°C	25°C
JG	1050 mW	8.4 mW/°C	25°C
P	1200 mW	9.6 mW/°C	25°C

recommended operating conditions (see Note 6)

	SERIES 55450B			SERIES 75451B			UNIT
	MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, V_{CC}	4.5	5	5.5	4.75	5	5.25	V
High-level input voltage, V_{IH}	2.2			2			V
Low-level input voltage, V_{IL}			0.8			0.8	V
Operating free-air temperature, T_A	−55		125	0		70	°C

NOTE 6: For the SN55450B only, the substrate (pin 8) must always be at the most negative device voltage for proper operation.

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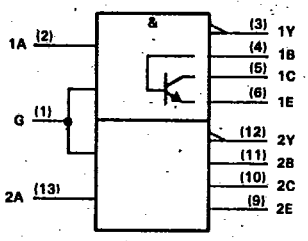
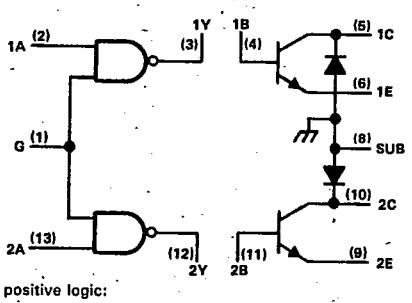
SN55450B
DUAL PERIPHERAL POSITIVE-AND DRIVER

logic symbol†



†This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



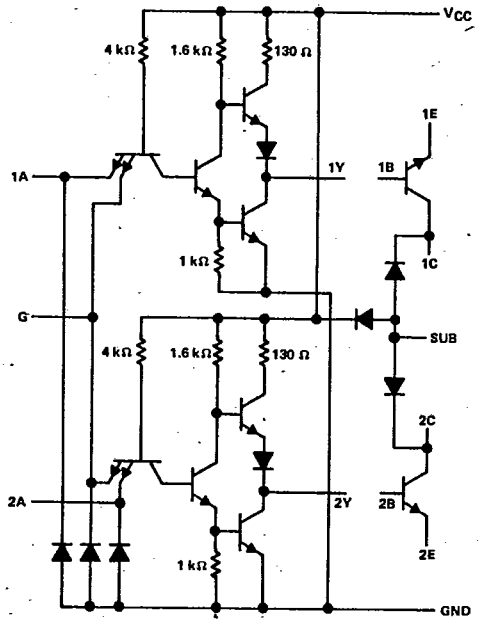
positive logic:

$Y = \overline{AG}$ or $\overline{A} + \overline{G}$ (gate only)

$C = AG$ or $\overline{\overline{A} + \overline{G}}$ (gate and transistor)

Pin numbers shown are for the J package.

schematic



Resistor values shown are nominal.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

TTL gates

PARAMETER			TEST CONDITIONS‡	SN55450B MIN	SN55450B TYP§	SN55450B MAX	UNIT
V_{IK}	Input clamp voltage		V_{CC} = MIN, I_I = −12 mA		−1.2	−1.5	V
V_{OH}	High-level output voltage		V_{CC} = MIN, V_{IL} = 0.8 V, I_{OH} = −400 μA	2.4	3.3		V
V_{OL}	Low-level output voltage		V_{CC} = MIN, V_{IH} = MIN, I_{OL} = 16 mA		0.25	0.5	V
I_I	Input current at maximum input voltage	input A	V_{CC} = MAX, V_I = 5.5 V			1	mA
		input G				2	
I_{IH}	High-level input current	input A	V_{CC} = MAX, V_I = 2.4 V			40	μA
		input G				80	
I_{IL}	Low-level input current	input A	V_{CC} = MAX, V_I = 0.4 V			−1.6	mA
		input G				−3.2	
I_{OS}	Short-circuit output current¶		V_{CC} = MAX, V_O = 0	−18	−35	−55	mA
I_{CCH}	Supply current, outputs high		V_{CC} = MAX, V_I = 0		2.8	4	mA
I_{CCL}	Supply current, outputs low		V_{CC} = MAX, V_I = 5 V		7	11	mA

‡For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

§All typical values are at V_{CC} = 5 V, T_A = 25°C.

¶Not more than one output should be shorted at a time.

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SN55450B
DUAL PERIPHERAL POSITIVE-AND DRIVER

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

output transistors

PARAMETER		TEST CONDITIONS†		SN55450B MIN	SN55450B TYP‡	SN55450B MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C = 100 μA, I_E = 0		35			V
$V_{(BR)CER}$	Collector-emitter breakdown voltage	I_C = 100 μA, R_{BE} = 500 Ω		30			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E = 100 μA, I_C = 0		5			V
h_{FE}	Static forward current transfer ratio	V_{CE} = 3 V, T_A = 25°C, See Note 7	I_C = 100 mA	25			
			I_C = 300 mA	30			
		V_{CE} = 3 V, T_A = MIN, See Note 7	I_C = 100 mA	10			
			I_C = 300 mA	15			
V_{BE}	Base-emitter voltage	I_B = 10 mA, I_C = 100 mA, See Note 7			0.85	1.2	V
		I_B = 30 mA, I_C = 300 mA, See Note 7			1	1.4	
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_B = 10 mA, I_C = 100 mA, See Note 7			0.25	0.5	V
		I_B = 30 mA, I_C = 300 mA, See Note 7			0.45	0.8	

†For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
‡All typical values are at V_{CC} = 5 V, T_A = 25°C.
NOTE 7: These parameters must be measured using pulse techniques. t_w = 300 μs, duty cycle ≤ 2%.

switching characteristics, V_{CC} = 5 V, T_A = 25°C

TTL gates

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	C_L = 15 pF, R_L = 400 Ω, See Figure 1		12		ns
t_{PHL}	Propagation delay time, high-to-low-level output			8		ns

output transistors

PARAMETER		TEST CONDITIONS§	MIN	TYP	MAX	UNIT
t_d	Delay time	I_C = 200 mA, $I_{B(1)}$ = 20 mA, $I_{B(2)}$ = −40 mA, $V_{BE(off)}$ = −1 V, C_L = 15 pF, R_L = 50 Ω, See Figure 2		8		ns
t_r	Rise time			12		ns
t_s	Storage time			7		ns
t_f	Fall time			6		ns

§Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

gate and transistors combined

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	I_C ≈ 200 mA, R_L = 50 Ω,	C_L = 15 pF, See Figure 3		20	30	ns
t_{PHL}	Propagation delay time, high-to-low-level output				20	30	ns
t_{TLH}	Transition time, low-to-high-level output				7	12	ns
t_{THL}	Transition time, high-to-low-level output				9	15	ns
V_{OH}	High-level output voltage after switching	V_S = 20 V, R_{BE} = 500 Ω,	I_C ≈ 300 mA, See Figure 4	V_S−6.5			mV

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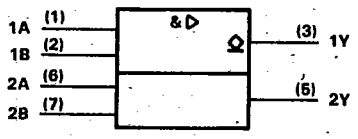
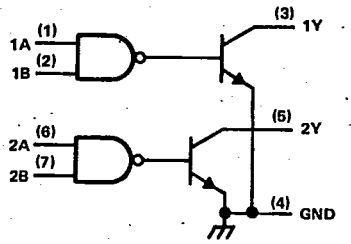
SN55451B, SN75451B
DUAL PERIPHERAL POSITIVE-AND DRIVERS

logic symbol†



†This symbol is in accordance with ANSI/IEEE STD 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)

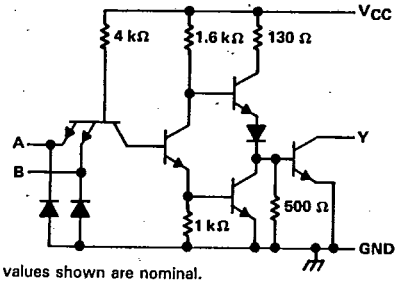


FUNCTION TABLE (EACH DRIVER)

A	B	Y
L	L	L (on state)
L	H	L (on state)
H	L	L (on state)
H	H	H (off state)

positive logic: $Y = AB$ or $\overline{\overline{A}+\overline{B}}$

schematic (each driver)



Pin numbers shown are for D, JG, and P packages.

Resistor values shown are nominal.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS‡	SN55451B MIN	SN55451B TYP§	SN55451B MAX	SN75451B MIN	SN75451B TYP§	SN75451B MAX	UNIT
V_{IK}	Input clamp voltage	V_{CC} = MIN, I_I = −12 mA		−1.2	−1.5		−1.2	−1.5	V
I_{OH}	High-level output current	V_{CC} = MIN, V_{IH} = MIN, V_{OH} = 30 V			300			100	μA
V_{OL}	Low-level output voltage	V_{CC} = MIN, V_{IL} = 0.8 V, I_{OL} = 100 mA		0.25	0.5		0.25	0.4	V
		V_{CC} = MIN, V_{IL} = 0.8 V, I_{OL} = 300 mA		0.5	0.8		0.5	0.7	
I_I	Input current at maximum input voltage	V_{CC} = MAX, V_I = 5.5 V			1			1	mA
I_{IH}	High-level input current	V_{CC} = MAX, V_I = 2.4 V			40			40	μA
I_{IL}	Low-level input current	V_{CC} = MAX, V_I = 0.4 V		−1	−1.6		−1	−1.6	mA
I_{CCH}	Supply current, outputs high	V_{CC} = MAX, V_I = 5 V		7	11		7	11	mA
I_{CCL}	Supply current, outputs low	V_{CC} = MAX, V_I = 0		52	65		52	65	mA

‡For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditons.
§All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	I_O ≈ 200 mA, C_L = 15 pF, R_L = 50 Ω, See Figure 3		18	25	ns
t_{PHL}	Propagation delay time, high-to-low-level output			18	25	ns
t_{TLH}	Transition time, low-to-high-level output			5	8	ns
t_{THL}	Transition time, high-to-low-level output			7	12	ns
V_{OH}	High-level output voltage after switching	V_S = 20 V, I_O ≈ 300 mA, See Figure 4	V_S−6.5			mV

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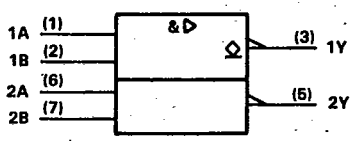
SN55452B, SN75452B
DUAL PERIPHERAL POSITIVE-NAND DRIVERS

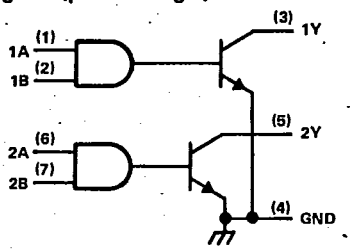
T-52-17

logic symbol†



†This symbol is in accordance with ANSI/IEEE STD 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)

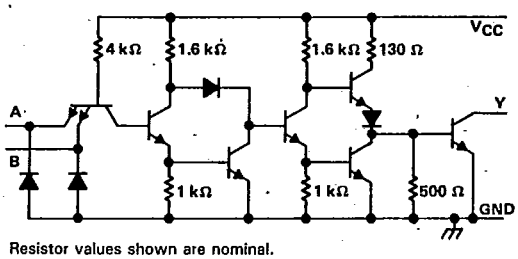


FUNCTION TABLE
(EACH DRIVER)

A	B	Y
L	L	H (off state)
L	H	H (off state)
H	L	H (off state)
H	H	L (on state)

positive logic:
$Y = \overline{AB}$ or $\overline{A}+\overline{B}$

schematic (each driver)



Pin numbers shown are for D, JG, and P packages.

Resistor values shown are nominal.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS‡	SN55452B MIN	SN55452B TYP§	SN55452B MAX	SN75452B MIN	SN75452B TYP§	SN75452B MAX	UNIT
V_{IK}	Input clamp voltage	V_{CC} = MIN, I_I = −12 mA		−1.2	−1.5		−1.2	−1.5	V
I_{OH}	High-level output current	V_{CC} = MIN, V_{IL} = 0.8 V, V_{OH} = 30 V			300			100	μA
V_{OL}	Low-level output voltage	V_{CC} = MIN, V_{IH} = MIN, I_{OL} = 100 mA		0.25	0.5		0.25	0.4	V
		V_{CC} = MIN, V_{IH} = MIN, I_{OL} = 300 mA		0.5	0.8		0.5	0.7	
I_I	Input current at maximum input voltage	V_{CC} = MAX, V_I = 5.5 V			1			1	mA
I_{IH}	High-level input current	V_{CC} = MAX, V_I = 2.4 V			40			40	μA
I_{IL}	Low-level input current	V_{CC} = MAX, V_I = 0.4 V		−1.1	−1.6		−1.1	−1.6	mA
I_{CCH}	Supply current, outputs high	V_{CC} = MAX, V_I = 0		11	14		11	14	mA
I_{CCL}	Supply current, outputs low	V_{CC} = MAX, V_I = 5 V		56	71		56	71	mA

‡For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§All typical values are at V_{CC} = 5 V, T_A = 25°C.

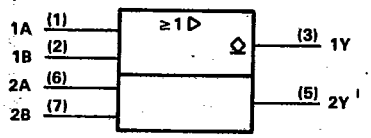
switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	I_O ≈ 200 mA, C_L = 15 pF, R_L = 50 Ω, See Figure 3		26	35	ns
t_{PHL}	Propagation delay time, high-to-low-level output			24	35	ns
t_{TLH}	Transition time, low-to-high-level output			5	8	ns
t_{THL}	Transition time, high-to-low-level output			7	12	ns
V_{OH}	High-level output voltage after switching	V_S = 20 V, I_O ≈ 300 mA, See Figure 4	V_S−6.5			mV

SN55453B, SN75453B
DUAL PERIPHERAL POSITIVE-OR DRIVERS

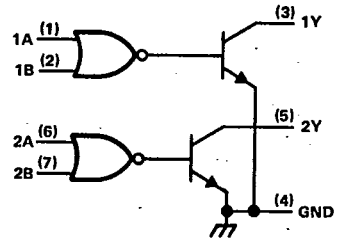
T-52-17

logic symbol†



†This symbol is in accordance with ANSI/IEEE STD 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)

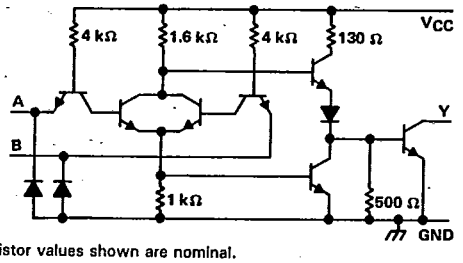


FUNCTION TABLE
(EACH DRIVER)

A	B	Y
L	L	L (on state)
L	H	H (off state)
H	L	H (off state)
H	H	H (off state)

positive logic:
$Y = A + B$ or $\overline{\overline{A}\,\overline{B}}$

schematic (each driver)



Pin numbers shown are for D, JG, and P packages.

Resistor values shown are nominal.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS‡		SN55453B			SN75453B			UNIT
				MIN	TYP§	MAX	MIN	TYP§	MAX	
V_{IK}	Input clamp voltage	V_{CC} = MIN,	I_I = −12 mA		−1.2	−1.5		−1.2	−1.5	V
I_{OH}	High-level output current	V_{CC} = MIN, V_{IH} = MIN, V_{OH} = 30 V				300			100	μA
V_{OL}	Low-level output voltage	V_{CC} = MIN, V_{IL} = 0.8 V, I_{OL} = 100 mA			0.25	0.5		0.25	0.4	V
		V_{CC} = MIN, V_{IL} = 0.8 V, I_{OL} = 300 mA			0.5	0.8		0.5	0.7	
I_I	Input current at maximum input voltage	V_{CC} = MAX,	V_I = 5.5 V			1			1	mA
I_{IH}	High-level input current	V_{CC} = MAX,	V_I = 2.4 V			40			40	μA
I_{IL}	Low-level input current	V_{CC} = MAX,	V_I = 0.4 V		−1	−1.6		−1	−1.6	mA
I_{CCH}	Supply current, outputs high	V_{CC} = MAX,	V_I = 5 V		8	11		8	11	mA
I_{CCL}	Supply current, outputs low	V_{CC} = MAX,	V_I = 0		54	68		54	68	mA

‡For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	I_O ≈ 200 mA, R_L = 50 Ω,	C_L = 15 pF, See Figure 3		18	25	ns
t_{PHL}	Propagation delay time, high-to-low-level output				16	25	ns
t_{TLH}	Transition time, low-to-high-level output				5	8	ns
t_{THL}	Transition time, high-to-low-level output				7	12	ns
V_{OH}	High-level output voltage after switching	V_S = 20 V, See Figure 4	I_O ≈ 300 mA,	V_S−6.5			mV

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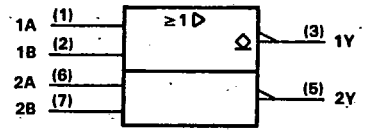
SN55454B, SN75454B
DUAL PERIPHERAL POSITIVE-NOR DRIVERS

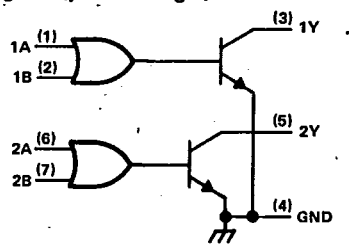
T-52-17

logic symbol†



†This symbol is in accordance with ANSI/IEEE STD 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)

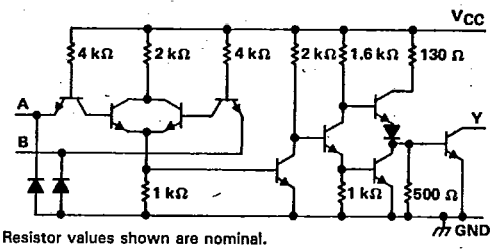


FUNCTION TABLE (EACH DRIVER)

A	B	Y
L	L	H (off state)
L	H	L (on state)
H	L	L (on state)
H	H	L (on state)

positive logic:
$Y = \overline{A+B}$ or $\overline{AB}$

schematic (each driver)



Pin numbers shown are for D, JG, and P packages.

Resistor values shown are nominal.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS‡	SN55454B MIN	SN55454B TYP§	SN55454B MAX	SN75454B MIN	SN75454B TYP§	SN75454B MAX	UNIT
V_{IK}	Input clamp voltage	V_{CC} = MIN, I_I = −12 mA		−1.2	−1.5		−1.2	−1.5	V
I_{OH}	High-level output current	V_{CC} = MIN, V_{IL} = 0.8 V, V_{OH} = 30 V			300			100	μA
V_{OL}	Low-level output voltage	V_{CC} = MIN, V_{IH} = MIN, I_{OL} = 100 mA		0.25	0.5		0.25	0.4	V
		V_{CC} = MIN, V_{IH} = MIN, I_{OL} = 300 mA		0.5	0.8		0.5	0.7	
I_I	Input current at maximum input voltage	V_{CC} = MAX, V_I = 5.5 V			1			1	mA
I_{IH}	High-level input current	V_{CC} = MAX, V_I = 2.4 V			40			40	μA
I_{IL}	Low-level input current	V_{CC} = MAX, V_I = 0.4 V		−1	−1.6		−1	−1.6	mA
I_{CCH}	Supply current, outputs high	V_{CC} = MAX, V_I = 0		13	17		13	17	mA
I_{CCL}	Supply current, outputs low	V_{CC} = MAX, V_I = 5 V		61	79		61	79	mA

‡For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§All typical values are at V_{CC} = 5 V, T_A = 25°C.

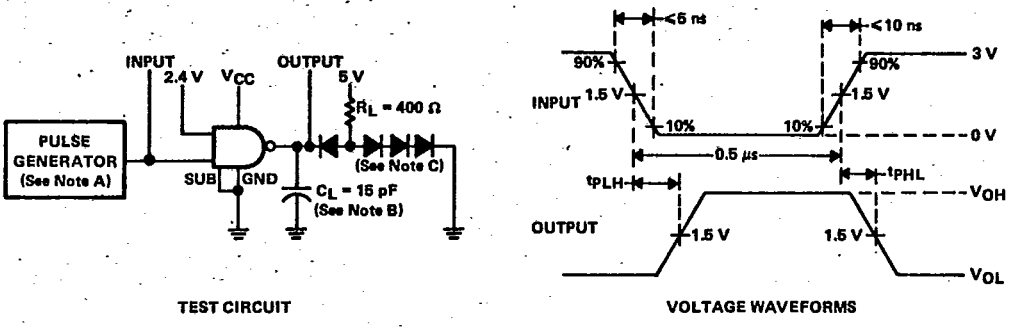
switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	I_O ≈ 200 mA, C_L = 15 pF, R_L = 50 Ω, See Figure 3		27	35	ns
t_{PHL}	Propagation delay time, high-to-low-level output			24	35	ns
t_{TLH}	Transition time, low-to-high-level output			5	8	ns
t_{THL}	Transition time, high-to-low-level output			7	12	ns
V_{OH}	High-level output voltage after switching	V_S = 20 V, I_O ≈ 300 mA, See Figure 4	V_S−6.5			mV

SN55450B
DUAL PERIPHERAL DRIVER

T-52-17

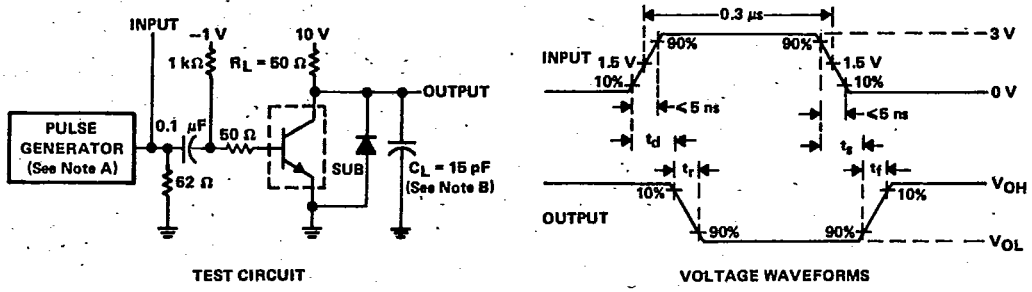
PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT VOLTAGE WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: PRR ≤ 1 MHz, Z_{out} ≈ 50 Ω.
B. C_L includes probe and jig capacitance.
C. All diodes are 1N3064.

FIGURE 1. PROPAGATION DELAY TIMES, EACH GATE (SN55450B ONLY)



TEST CIRCUIT VOLTAGE WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: duty cycle ≤ 1%, Z_{out} ≈ 50 Ω.
B. C_L includes probe and jig capacitance.

FIGURE 2. SWITCHING TIMES, EACH TRANSISTOR (SN55450B ONLY)

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PARAMETER MEASUREMENT INFORMATION

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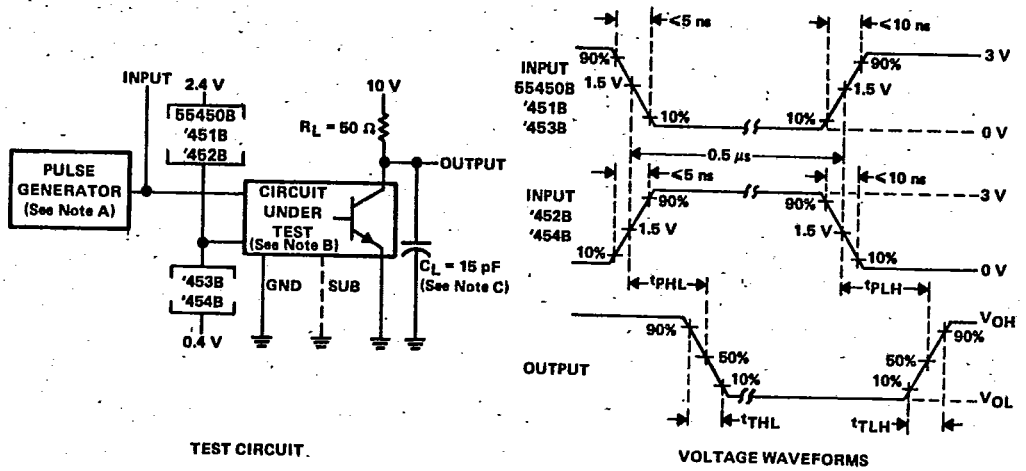
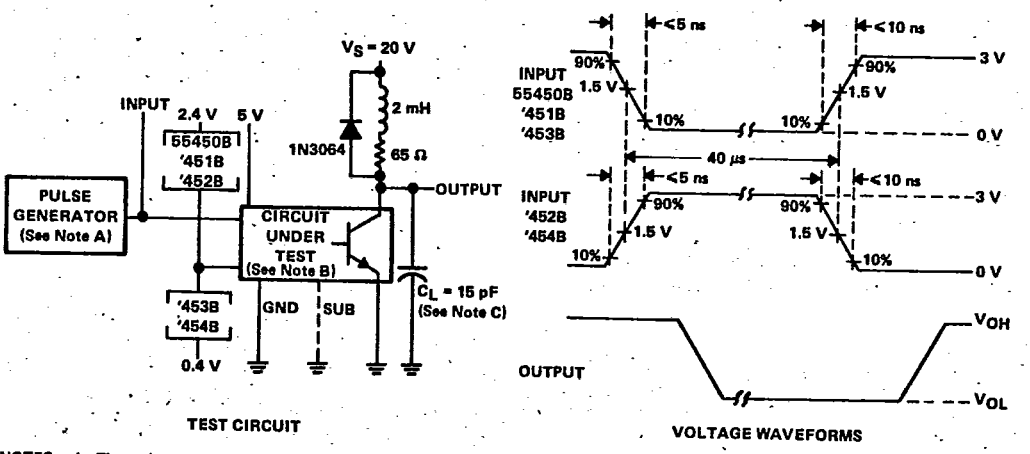


TEST CIRCUIT

VOLTAGE WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: PRR ≤ 1 MHZ, Z_{out} ≈ 50 Ω.
B. When testing SN55450B, connect output Y to transistor base and ground the substrate terminal.
C. C_L includes probe and jig capacitance.

FIGURE 3. SWITCHING TIMES OF COMPLETE DRIVERS



TEST CIRCUIT

VOLTAGE WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: PRR ≤ 12.5 kHz, Z_{out} = 50 Ω.
B. When testing SN55450B, connect output Y to transistor base with a 500-Ω resistor from there to ground, and ground the substrate terminal.
C. C_L includes probe and jig capacitance.

FIGURE 4. LATCH-UP TEST OF COMPLETE DRIVERS

5 Peripheral Drivers/Actuators

TYPICAL CHARACTERISTICS

SN55450B
TTL GATE
HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT

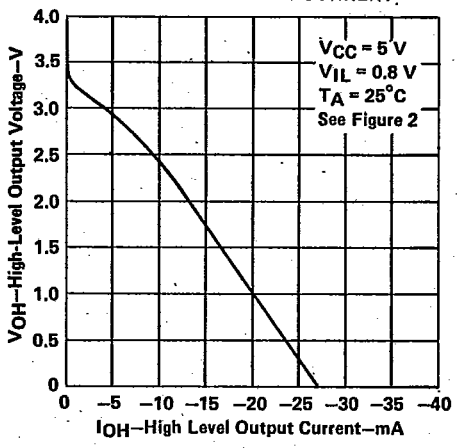


FIGURE 5

SN55450B
TRANSISTOR
STATIC FORWARD CURRENT TRANSFER RATIO
vs
COLLECTOR CURRENT

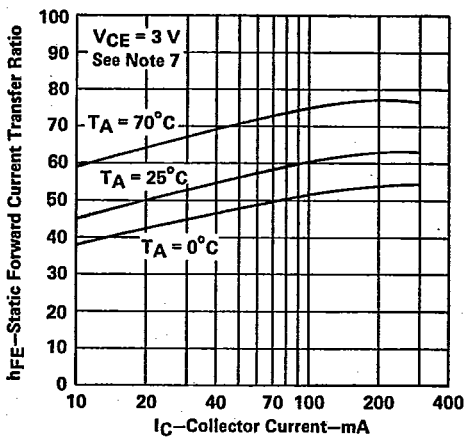


FIGURE 6

SN55450B
TRANSISTOR
BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT

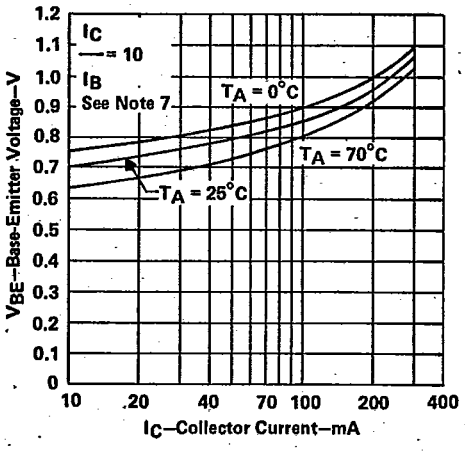


FIGURE 7

TRANSISTOR
COLLECTOR-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT

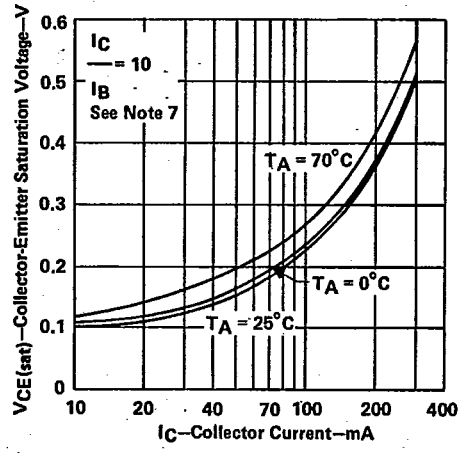


FIGURE 8

NOTE 7: These parameters must be measured using pulse techniques, t_w = 300 μs, duty cycle ≤2%.

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